

Application Serial No. 10/615,899
Reply to office action of September 23, 2005

PATENT
Docket: CU-3282

Amendments to the Claims

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

Listing of claims:

What is claimed is:

1. (Currently amended) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:

~~preparing a reaction unit using chlorine series gas; and~~
~~generating a plasma in the apparatus that includes including at least one of~~
~~hydrogen and nitrogen and 5% to 90% argon~~ in the reaction unit to remove a residual
~~remaining in a reaction tube~~ of the reaction unit.

2. (Cancelled)
3. (Cancelled)
4. (Cancelled)
5. (Cancelled)
6. (Cancelled)
7. (Cancelled)
8. (Cancelled)
9. (Cancelled)

Application Serial No. 10/615,899
Reply to office action of September 23, 2005

PATENT
Docket: CU-3282

10. (Cancelled)
11. (New) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:
generating a plasma in the apparatus that includes nitrogen and 5% to 90% hydrogen in the reaction unit to remove a residual remaining in a reaction tune tube of the reaction unit.
12. (New) A method for improving reliability of an etching apparatus and a deposition apparatus, which etching and deposition apparatus' use chlorine-containing etching and deposition gases respectively, the method comprising the steps of:
generating a plasma in the apparatus that includes hydrogen and nitrogen in the reaction unit to remove a residual remaining in a reaction tune tube of the reaction unit, wherein the plasma including nitrogen comprises hydrogen of 5 to 50% and argon of 5 to 90%.